

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**

(Use several sheets if necessary)

Application Number
09/910,447

Applicant

Toshihiko HIGUCHI

Filing Date
July 19, 2001

Group Art Unit
Not Assigned

U.S. PATENT DOCUMENTS

[illegible]

**COPY OF PAPERS
ORIGINALLY FILED**

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

12	"Reduction of Threshold Voltage Deviation in Damascene Metal Gate MOSFETs" by YAGISHITA, et al. / IEEE, 1999

EXAMINER

DATE CONSIDERED

21 May 02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.